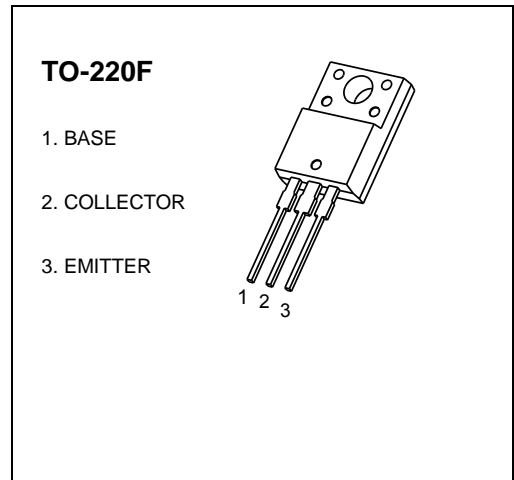


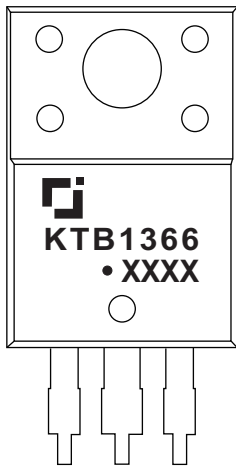
KTB1366 TRANSISTOR (PNP)

FEATURES

- Low $V_{CE(sat)}$: $V_{CE(sat)} = -1.0V(\text{Max.})(I_C/I_B = -2A/-0.2A)$
- Complementary to KTD2058

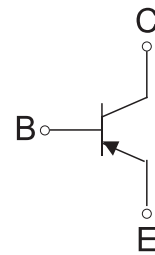


MARKING



KTB1366=Device code
 Solid dot=Green moldinn compound device,
 if none,the normal device
 XXXX=Code

Equivalent Circuit



MAXIMUM RATINGS ($T_a=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-60	V
V_{CEO}	Collector-Emitter Voltage	-60	V
V_{EBO}	Emitter-Base Voltage	-7	V
I_C	Collector Current -Continuous	-3	A
P_C	Collector power dissipation	2	W
T_J, T_{stg}	Operation Junction and Storage Temperature Range	-55~+150	$^\circ\text{C}$

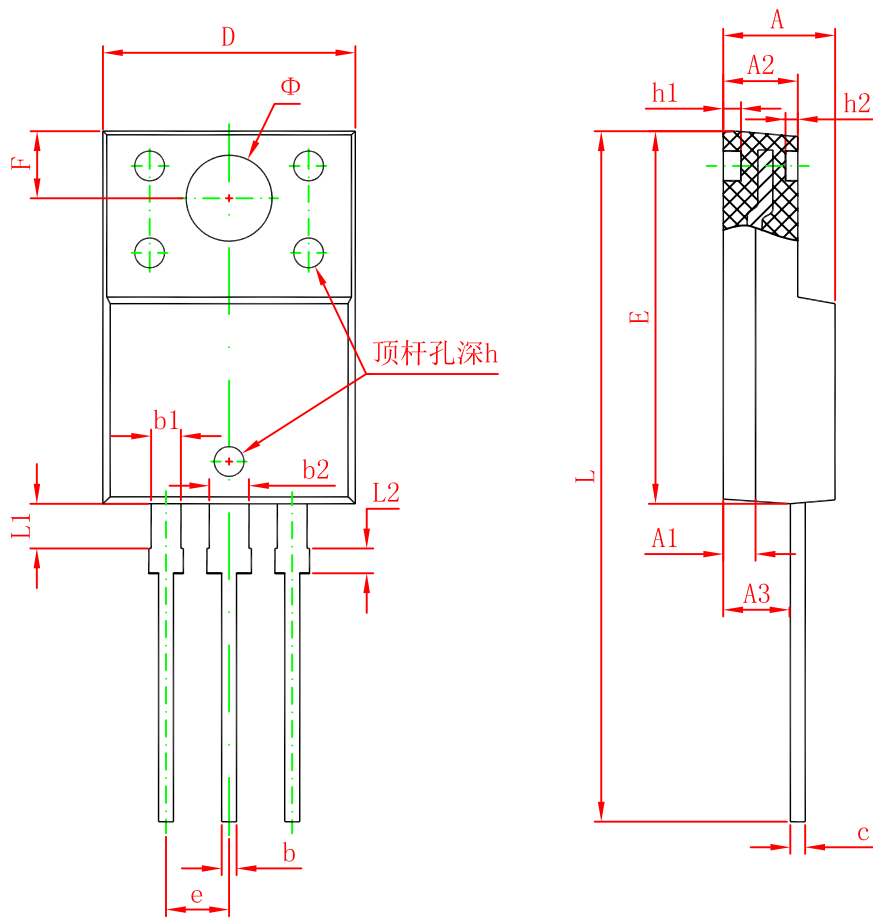
ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-1\text{mA}, I_E=0$	-60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-50\text{mA}, I_B=0$	-60			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-1\text{mA}, I_C=0$	-7			V
Collector cut-off current	I_{CBO}	$V_{CB}=-60\text{V}, I_E=0$			-100	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-7\text{V}, I_C=0$			-100	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=-5\text{V}, I_C=-0.5\text{A}$	60		200	
	$h_{FE(2)}$	$V_{CE}=-5\text{V}, I_C=-3\text{A}$	20			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-2\text{A}, I_B=-0.2\text{A}$			-1	V
Base-emitter voltage	V_{BE}	$V_{CE}=-5\text{V}, I_C=-0.5\text{A}$			-1	V
Transition frequency	f_T	$V_{CE}=-5\text{V}, I_C=-0.5\text{A}$		9		MHz
Collector output capacitance	C_{ob}	$V_{CB}=-10\text{V}, I_E=0, f=1\text{MHz}$		150		pF
Fall time	t_f	$I_C=-2\text{A}, I_{B1}=-I_{B2}=-0.2\text{A}$ $V_{CC}=-30\text{V}$		0.4		μs
Storage time	t_s			1.7		μs

CLASSIFICATION of $h_{FE(1)}$

Rank	O	Y
Range	60-120	100-200

TO-220F Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.300	4.700	0.169	0.185
A1	1.300 REF.		0.051 REF.	
A2	2.800	3.200	0.110	0.126
A3	2.500	2.900	0.098	0.114
b	0.500	0.750	0.020	0.030
b1	1.100	1.350	0.043	0.053
b2	1.500	1.750	0.059	0.069
c	0.500	0.750	0.020	0.030
D	9.960	10.360	0.392	0.408
E	14.800	15.200	0.583	0.598
e	2.540 TYP.		0.100 TYP.	
F	2.700 REF.		0.106 REF.	
Φ	3.500 REF.		0.138 REF.	
h	0.000	0.300	0.000	0.012
h1	0.800 REF.		0.031 REF.	
h2	0.500 REF.		0.020 REF.	
L	28.000	28.400	1.102	1.118
L1	1.700	1.900	0.067	0.075
L2	0.900	1.100	0.035	0.043

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